

350V P-Channel MOSFET

General Features

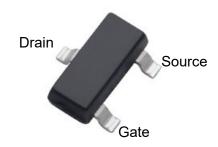
- ➤ ESD improved Capability
- Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure
- Fast Switching Speed
- RoHS Compliant
- ➤ Halogen-free available

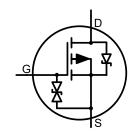
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Ap	plica	ıtions

- ➤ High Efficiency SMPS
- ➤ Adaptor/Charger
- Active PFC

BVDSX	RDS(ON) (Max.)	ID
-350V	30 Ω	-200mA

SOT-23





Ordering Information

Part Number Package		Marking	Remark
FTZ30P35G	8		Halogen Free

Absolute Maximum Ratings

T_A=25°C unless otherwise specified

Symbol	Parameter	FTZ30P35G	Unit	
V_{DSX}	Drain-to-Source Voltage ^[1]	-350	V	
V _{DGX}	Drain-to-Gate Voltage ^[1]	-350	V	
I_D	Continuous Drain Current	-0.2	Δ.	
I_{DM}	Pulsed Drain Current ^[2]	-0.6	A	
P_{D}	Power Dissipation	0.50	W	
V_{GS}	Gate-to-Source Voltage	±20	V	
V _{ESD(G-S)}	Gate Source ESD IEC, C=150pF, R=330 Ω	350	V	
$T_{\rm L}$	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300	$^{\circ}$	
T _J and T _{STG}	Operating and Storage Temperature Range	-55 to 150		

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	FTZ30P35G	Unit
$R_{ heta JA}$	Thermal Resistance, Junction-to-Ambient	250	K/W

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Electrical Characteristics

OFF Characteristics

 $T_A = 25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSX}	Drain-to-Source Breakdown Voltage	-350			V	$V_{GS}=0V, I_{D}=-250\mu A$
$\triangle BV_{DSS}/\triangle T_{J}$	Breakdown Voltage Temperature Coefficient		-0.35		V/℃	Reference to 25° C, I_D =- $250\mu A$
				-1	μΑ	V_{DS} =-350V, V_{GS} = 0V
I_{DSS}	Drain-to-Source Leakage Current			-100	uA	V_{DS} =-350V, V_{GS} = 0V T_J =125°C
I _{GSS}	Gate-to-Source Leakage Current	-		20	uA	V _{GS} =+20V, V _{DS} =0V
				-20		V_{GS} =-20V, V_{DS} =0V

ON Characteristics

$T_A = 25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
R _{DS(ON)}	Static Drain-to-Source On-Resistance		18	30	Ω	V_{GS} =-10V, I_D =-200mA [3]
V _{GS(TH)}	Gate Threshold Voltage	-1		-3	V	$V_{GD} = 0V, I_D = -250 \mu A$

Dynamic Characteristics

Essentially independent of operating temperature

<u> </u>						one of operating temperature
Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
C_{ISS}	Input Capacitance		43.39		pF	V_{GS} =0V V_{DS} =-25V f =1.0MH $_Z$
Coss	Oput Capacitance		6.94			
C_{RSS}	Reverse Transfer Capacitance		0.84			
$t_{d(ON)}$	Turn-on Delay Time		12		ns	$V_{GS} = -10V \sim 0V$ $V_{DD} = -25V, I_D = -80mA$ $R_G = 25Ohm$
t_{rise}	Rise Time		60			
$t_{d(OFF)}$	Turn-off Delay Time		136			
t_{fall}	Fall Time		320			

Source-Drain Diode Characteristics

T_A=25°C unless otherwise specified

Source Brain Blode Characteristics			TA 25 C unless otherwise specified			
Symbol	Parameter	Min	Тур.	Max.	Units	Test Conditions
$ m V_{SD}$	Diode Forward Voltage			-1.8	V	I_{SD} =-200 mA, V_{GS} =0 V

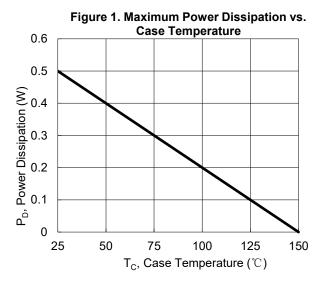
NOTE:

- [1] $T_J = +25^{\circ}C$ to $+150^{\circ}C$
- [2] Repetitive rating, pulse width limited by maximum junction temperature.
- [3] Pulse width \(380\mu s; \) duty cycle \(\le 2\%.

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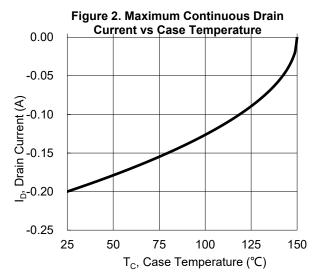
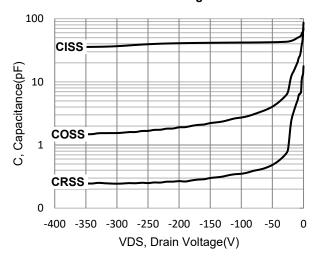


Figure 3. Typical Capacitance vs. Drain-to-Source Voltage



Switching Waveforms and Test Circuit

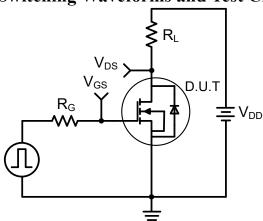


Figure 4. Resistive Switching Test Circuit

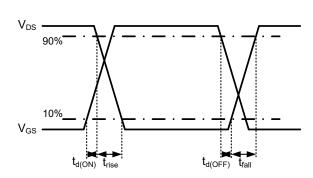
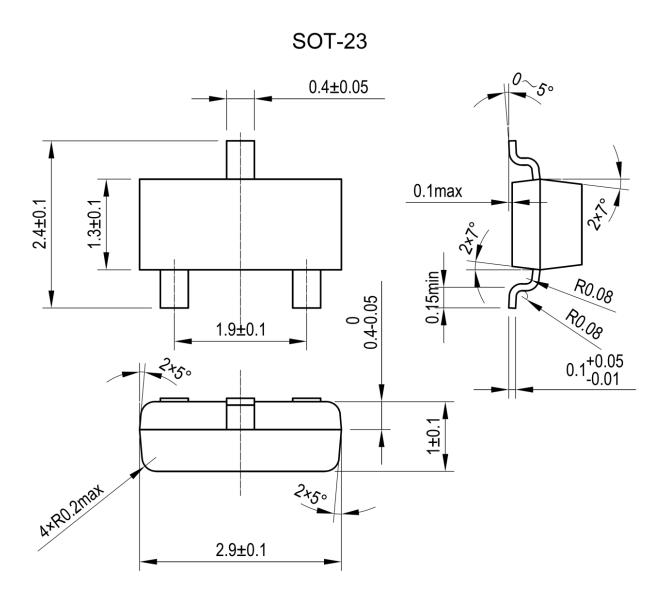


Figure 5. Resistive Switching Waveforms

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Package Dimensions





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